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(54) Title: DUAL CURE B-STAGEABLE UNDERFILL FOR WAFER LEVEL

(57) Abstract: A silicon wafer has a B-stageable underfill material deposited on the active face of the wafer. The B-stageable underfill comprises a first composition with a lower curing temperature and a second composition with a higher curing temperature, characterized in that the first composition has been fully cured.

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